

Ⓢ Pending

Active

- ✎ L12: (16352) sheet adj resistance
- ✎ L13: (10262) source near resistance

L14 (25547) L12 L13

2115 (476) atox

2 L16: (31) L15 a

→ L17: (557393) (FOX file)

➔ L18: (1177740) (perpendicular \$2 or thoponal\$3)

*L18: (1783) L17 near 6 L18

→ L20: (20) L15 and L19

L21: (49) 16 20

☎ 122: (2687685)

☛ L23: (47) 21 and 17

② L24: (47) 23 and 22

☛ L25: (9) Backward c

➤ L26: (3) Forward citation search 4

➡ L27: (57528) source near (line con

→ L28: (1863886) buried substrate

L29: (461) 27 near 28

☞ L30: (841) 27 near 8 1

☞ L31: (354) 28 same 30

2132 (4) 29 same 30

☞ L33: (41) 32 and 27

☛ L34: (41) 33 and 17

✖ Failed

U	I	Inventory	Document	Issue	P	Title	Current	Current X	Retrieval	S	C	P	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54	55	56	57	58	59	60	61	62	63	64	65	66	67	68	69	70	71	72	73	74	75	76	77	78	79	80	81	82	83	84	85	86	87	88	89	90	91	92	93	94	95	96	97	98	99	100
---	---	-----------	----------	-------	---	-------	---------	-----------	-----------	---	---	---	---	---	---	---	---	---	---	---	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	----	-----

	R	Song, Yun-He	US 6835532	2003 1	Method for fabricating NOR type flash memoe	438/259	257/E21.68	P	C	F	I	C	US 6835532
	F	Lee, Robin et	US 6211012	2001 0	Method of fabricating an ETOX flash memory	438/257	257/E21.68	P	F	F	I	C	US 6211012
	F	Lee, Robin	US 6372584	2002 0	Method of manufacturing Vshaped flash me	438/192	257/E29.30	P	F	F	I	C	US 6372584
	D	Ding, Yi	US 2004022	2004 3	Formation of dielectric on a gate surface to	438/585	438/197.	P	C	F	I	C	US 2004022
	F	Ding, Yi	US 2004022	2004 3	FABRICATION OF GATE DIELECTRIC IN NON	438/257		P	C	F	I	C	US 2004022
	F	Ding, Yi	US 2004022	2004 3	FABRICATION OF GATE DIELECTRIC IN NON	257/315		P	C	F	I	C	US 2004022
	F	Ding, Yi	US 2004020	2004 5	NONVOLATILE MEMORIES WITH A FLOATIN	257/315	257/316;	P	C	F	I	C	US 2004020
	F	Ding, Yi	US 2004018	2004 0	Nonvolatile memories and methods of fabrica	438/257	438/258	P	C	F	I	C	US 2004018
	F	Ding, Yi	US 2004018	2004 0	Nonvolatile memories and methods of fabrica	438/257	257/316;	P	C	F	I	C	US 2004018
	F	Ding, Yi	US 2004018	2004 0	Fabrication of integrated circuit elements in	438/257		P	C	F	I	C	US 2004018

[FRS](#)
[Details](#)
[HTML](#)

100

PRINTED